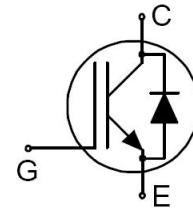


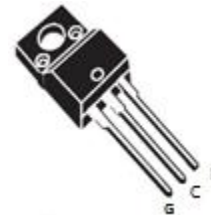
600V , 19A , Trench-FS IGBT

Features

- ◆ Advanced Trench+FS (Field Stop) IGBT technology
- ◆ Low Collector-Emitter Saturation voltage, typical data is 1.7V @ 19A.
- ◆ Easy parallel switching capability due to positive Temperature coefficient in Vce.
- ◆ 10uS short-circuit
- ◆ Fast switching
- ◆ High input impedance
- ◆ Pb- Free product



Schematic Diagram



TO-220F

Applications

- ◆ General general-purpose inverter
- ◆ Motor control
- ◆ Intelligent power module.

Electrical characteristics(T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test conditions	Units	Min.	Typ.	Max.
V _{(BR)CES}	Collector - Emitter breakdown voltage	V _{GE} = 0V, I _C =250uA	V	600	—	—
V _{CE(sat)}	Collector-Emitter Saturation voltage	V _{GE} =15V, I _C =19A,T _C =25°C	V	—	1.7	2.0
		V _{GE} =15V, I _C =19A,T _C =125°C	V	—	2.05	—
V _{GE(th)}	Gate threshold voltage	V _{GE} = V _{CE} , I _C = 0.25mA	V	4.0	5.0	6.5
V _f	Diode forward voltage	I _F =19A	V	—	1.6	2.0
I _{GES}	Gate to Emitter Forward Leakage	V _{GE} =+30V	nA	—	—	200
I _{GESR}	Gate to Emitter reverse Leakage	V _{GE} =-30V		-200	—	—
I _{CES}	Zero gate voltage collector current	V _{CE} =600V	uA	—	—	25